

Notice of References Cited		Application/Control No.	Applicant(s)/Patent Under Reexamination	
		10/711,004	CHANG, KENT KUOHUA	
Examiner		Art Unit		Page 1 of 1
Maria Guerrero		2822		

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	M	US-			

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Kang et al. "Improved Thermal Stability and device performance of ultra-thin (EOT<10A) gate dielectric MOSFETs by using hafnium oxynitride (HfO _x N _y)"; June 2002; IEEE, pages 146-147.
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	X	Shanware et al. "Reliability evaluation of HfSiON gate dielectric film with 12.8 a SiO ₂ equivalent thickness"; December 2001

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.